



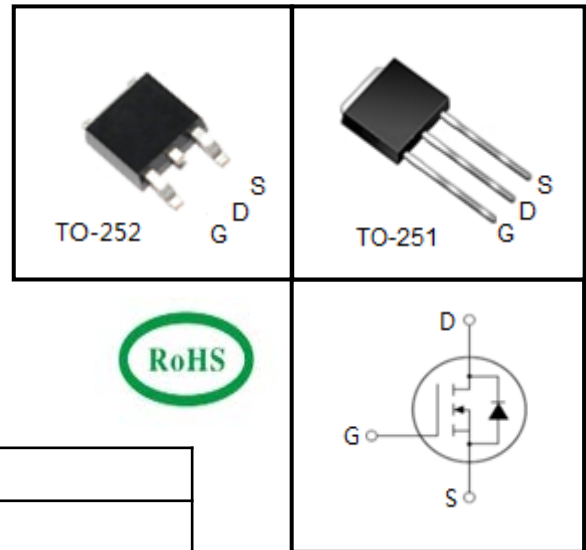
550V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Device	Package	Marking
TMD1N55HT	TO-252	D1N55HT
TMU1N55HT	TO-251	U1N55HT

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted				
Parameter	Symbol	Value		Unit
		TO-252	TO-251	
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	550		V
Continuous Drain Current	I_D	1		A
Pulsed Drain Current (note1)	I_{DM}	4		A
Gate-Source Voltage	V_{GSS}	± 25		V
Single Pulse Avalanche Energy (note2)	E_{AS}	22		mJ
Avalanche Current (note1)	I_{AR}	0.7		A
Repetitive Avalanche Energy (note1)	E_{AR}	3.7		mJ
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	17		W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150		$^\circ\text{C}$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-252	TO-251	
Thermal Resistance, Junction-to-Case	R_{thJC}	7.3		$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60		



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	550	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 550V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 25V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.2	--	3.2	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.5A$	--	7	8	Ω
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0\text{MHz}$	--	170	--	pF
Output Capacitance	C_{oss}		--	19	--	
Reverse Transfer Capacitance	C_{rss}		--	3	--	
Total Gate Charge	Q_g	$V_{DD} = 440V, I_D = 1A,$ $V_{GS} = 10V$	--	4.5	--	nC
Gate-Source Charge	Q_{gs}		--	0.7	--	
Gate-Drain Charge	Q_{gd}		--	2.2	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 275V, I_D = 1A,$ $R_G = 25\Omega$	--	3.5	--	ns
Turn-on Rise Time	t_r		--	35	--	
Turn-off Delay Time	$t_{d(off)}$		--	19	--	
Turn-off Fall Time	t_f		--	64	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	0.9	A
Pulsed Diode Forward Current	I_{SM}		--	--	3.6	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 1A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	t_{rr}	$V_{GS} = 0V, I_S = 1A,$ $di_F/dt = 100A/\mu s$	--	72	--	ns
Reverse Recovery Charge	Q_{rr}		--	1.5	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_{AS} = 0.7A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$



Figure A: Gate Charge Test Circuit and Waveform

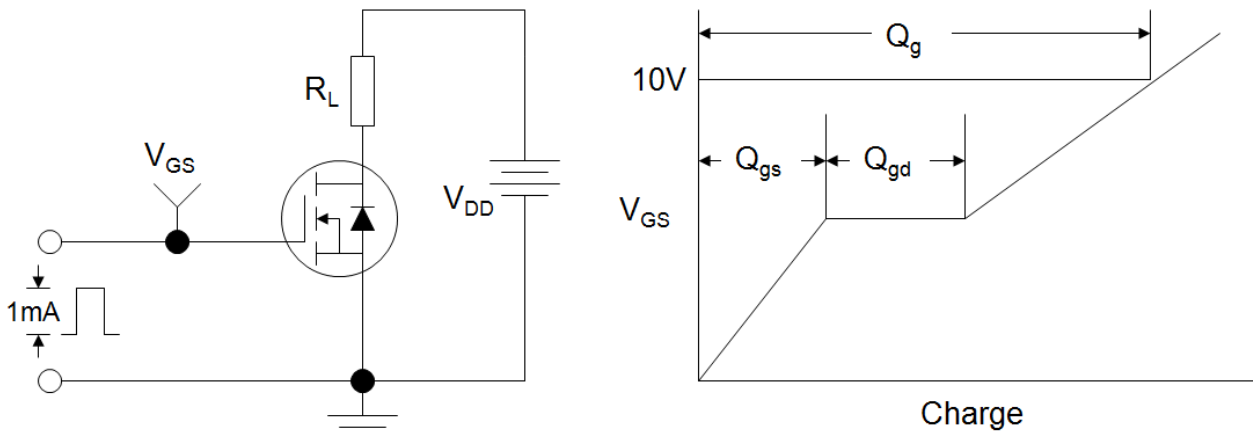
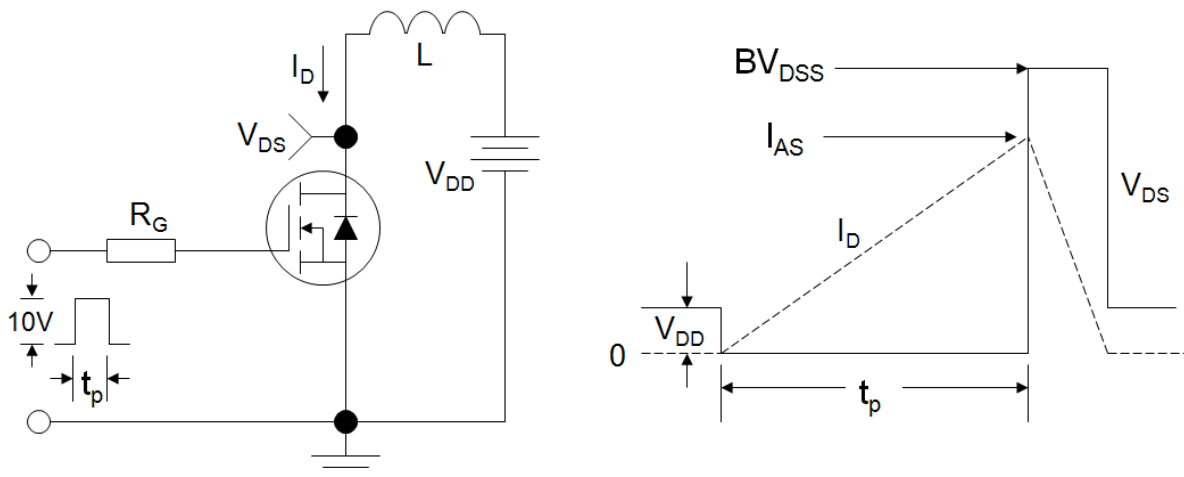


Figure B: Resistive Switching Test Circuit and Waveform

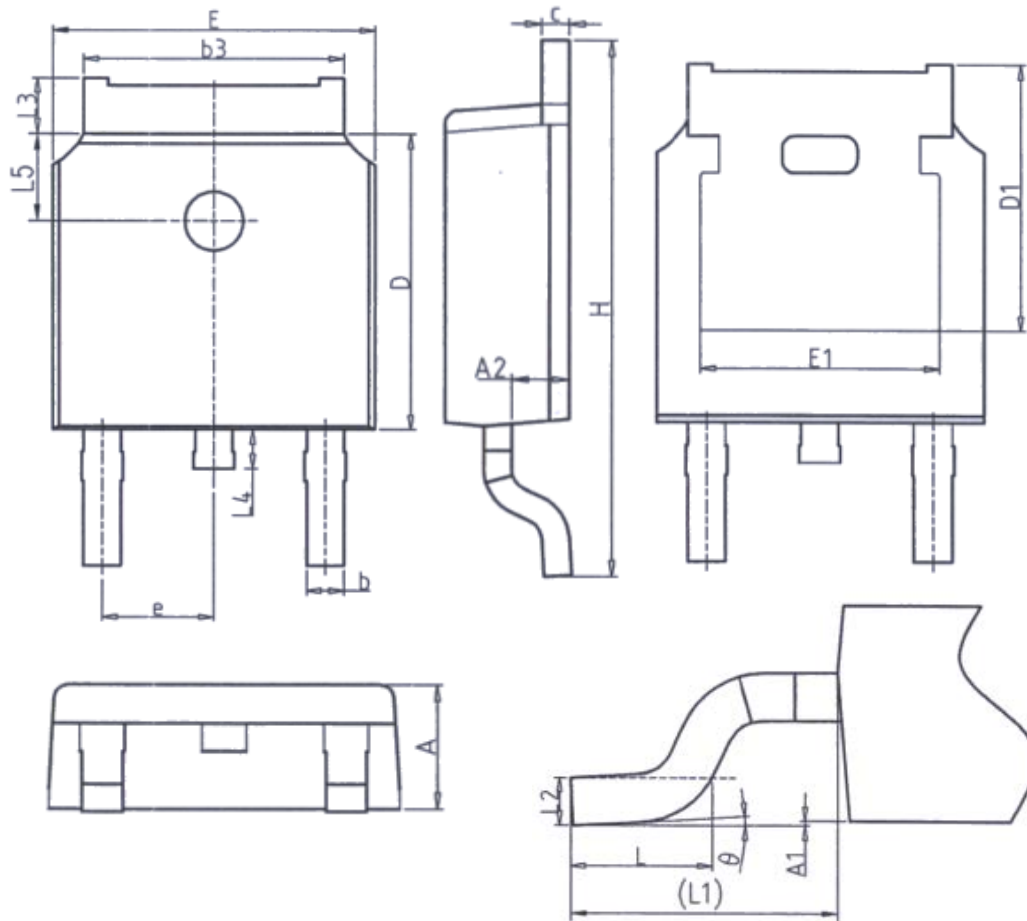


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-252

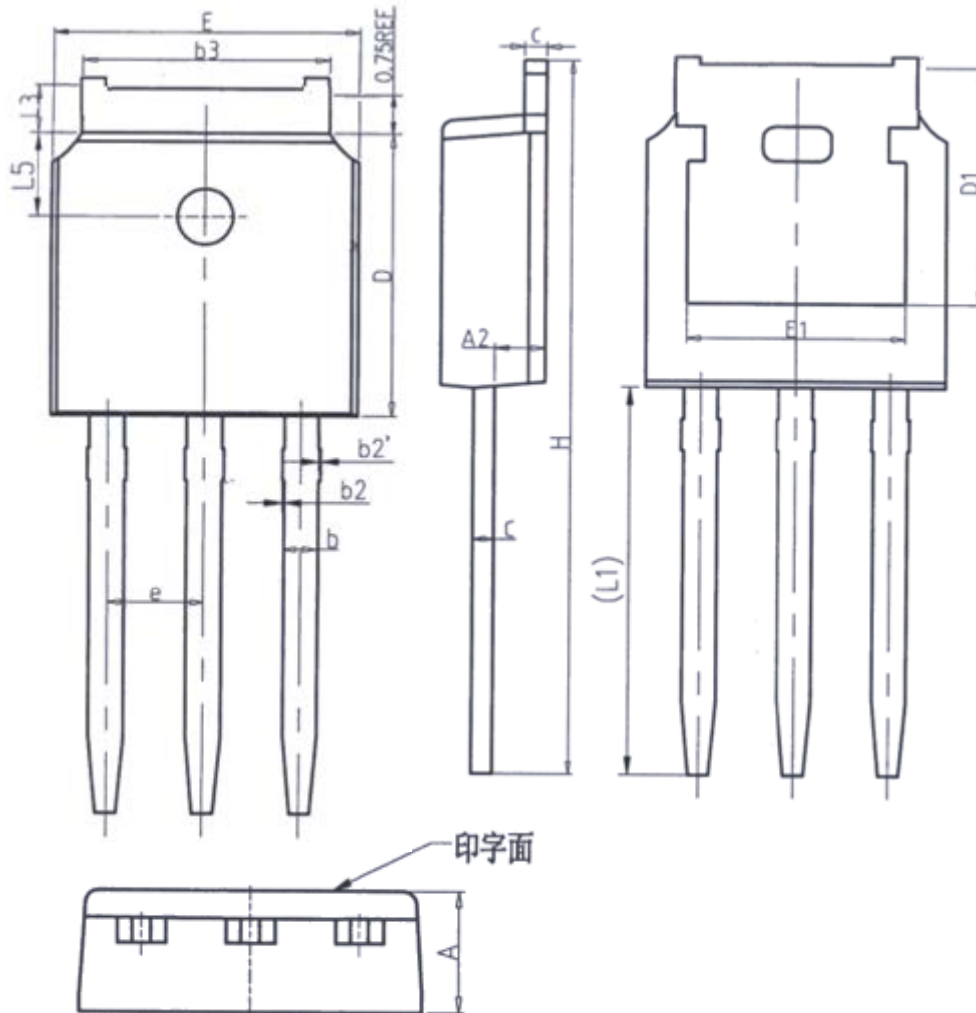


Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	-

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	-	1.00
L5	1.65	1.95
theta	0°	8°



TO-251



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2'	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95



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